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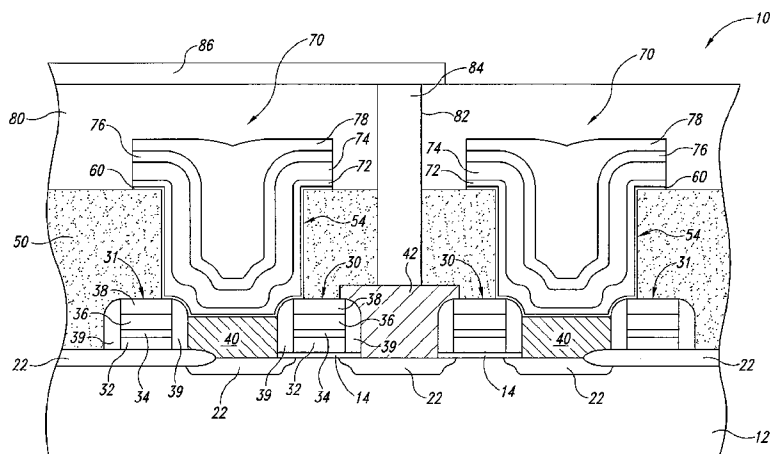
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(54) Title: ELECTRICAL COMPONENTS FOR MICROELECTRONIC DEVICES AND METHODS OF FORMING THE SAME



(57) Abstract: Electrical components for microelectronic devices and methods for forming electrical components. One particular embodiment of such a method comprises depositing an underlying layer onto a workpiece, and forming a conductive layer on the underlying layer. The method can continue by disposing a dielectric layer on the conductive layer. The underlying layer is a material that causes the dielectric layer to have a higher dielectric constant than without the underlying layer being present under the conductive layer. For example, the underlying layer can impart a structure or another property to the film stack that causes an otherwise amorphous dielectric layer to crystallize without having to undergo a separate high temperature annealing process after disposing the dielectric layer onto the conductive layer. Several examples of this method are expected to be very useful for forming dielectric layers with high dielectric constants because they avoid using a separate high temperature annealing process.

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